



# N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

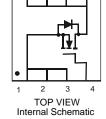
- Case: DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.0172 grams (approximate)

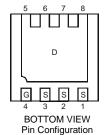


TOP VIEW



**BOTTOM VIEW** 





**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	ID	7.62 4.83	А
Pulsed Drain Current (Note 4)			$I_{DM}$	45.9	A

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P <sub>D</sub>	0.99	W
Thermal Resistance, Junction to Ambient @TA = 25°C (Note 3)	$R_{ heta JA}$	126.7	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
  3. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

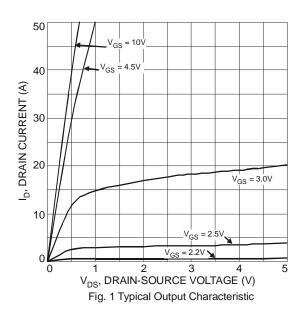


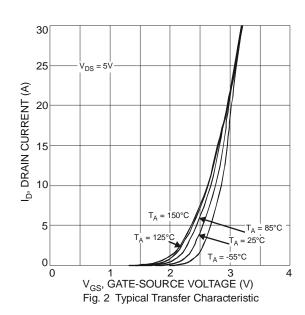
## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	-	2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	OS (ON)	10 15	15	mΩ	$V_{GS} = 10V, I_D = 11.6A$	
Static Drain-Source On-Nesistance	KDS (ON)		17	23.5		$V_{GS} = 4.5V, I_D = 10A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	8	-	S	$V_{DS} = 10V, I_{D} = 9A$	
Diode Forward Voltage	$V_{SD}$	-	0.7	1.0	V	$V_{GS} = 0V$ , $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C <sub>iss</sub>	-	867	-	pF		
Output Capacitance	Coss	-	85	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	$C_{rss}$	-	81	-	pF	1 = 1.000112	
Gate Resistance	$R_{g}$	-	1.39	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	-	18.85	-	nC	V 40V V 45V	
Gate-Source Charge	$Q_{gs}$	-	2.59	-	nC	$V_{GS} = 10V, V_{DS} = 15V,$	
Gate-Drain Charge	$Q_{gd}$	-	6.15	-	nC	I <sub>D</sub> = 11.6A	
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.46	-	ns	45)/ )/ 40)/	
Turn-On Rise Time	t <sub>r</sub>	-	14.53	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_{L} = 1.3\Omega, R_{G} = 3\Omega,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	18.84	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	6.01	-	ns	$I_D = 1A$	

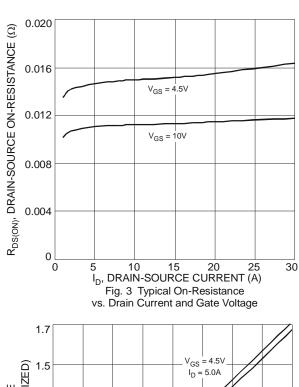
Notes:

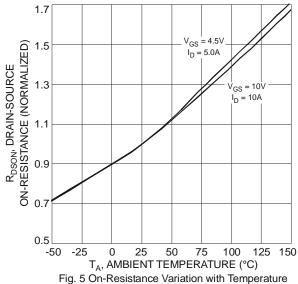
- 5. Short duration pulse test used to minimize self-heating effect.6. Guaranteed by design. Not subject to production testing.











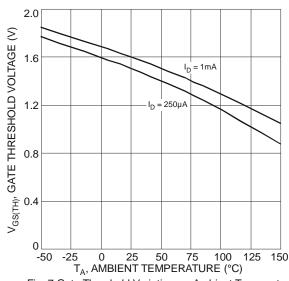
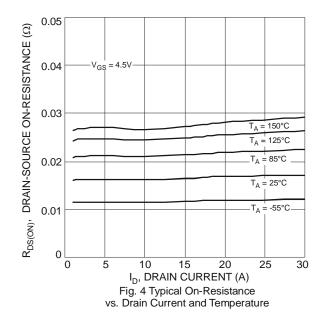
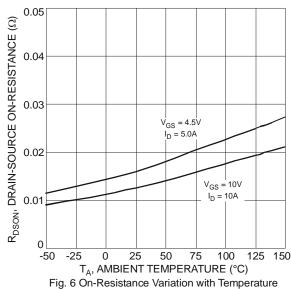
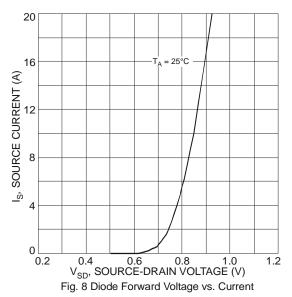


Fig. 7 Gate Threshold Variation vs. Ambient Temperature









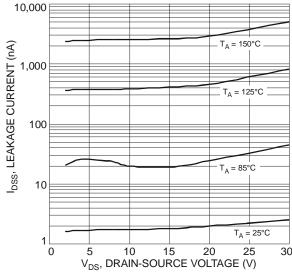
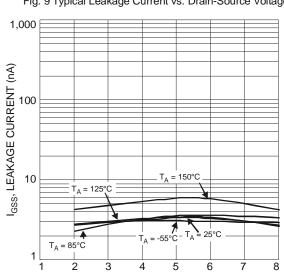
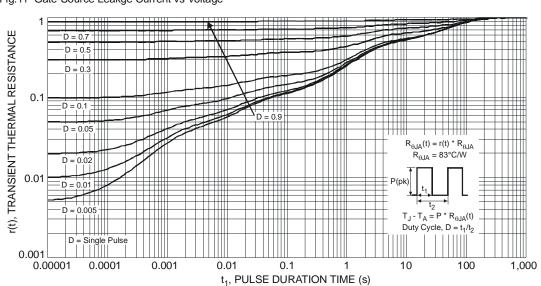


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage



 $\rm V_{GS},\, GATE\text{-}SOURCE\,\, VOLTAGE\,\, (V)$  Fig.11 Gate-Source Leakge Current vs Voltage



1,000

I<sub>GSS</sub>, LEAKAGE CURRENT (nA)

= 125°C

 $V_{GS}$ , GATE-SOURCE VOLTAGE (V)

Fig.10 Gate-Source Leakge Current vs Voltage

= 150°C

Fig. 12 Transient Thermal Response



### Ordering Information (Note 7)

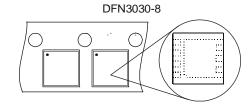
Part Number	Case	Packaging
DMG4468LFG-7	DFN3030-8	3000 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

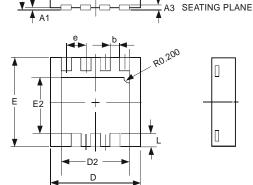
## **Marking Information**



N45 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year, ex: 09 for 2009 WW = Week code 01 to 52

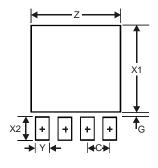


# **Package Outline Dimensions**



DFN3030-8				
Dim	Min	Max	Тур	
Α	0.57	0.63	0.60	
A1	0	0.05	0.02	
<b>A3</b>	_	_	0.15	
b	0.29	0.39	0.34	
D	2.90	3.10	3.00	
D2	2.19	2.39	2.29	
е	_	_	0.65	
Е	2.90	3.10	3.00	
E2	1.64	1.84	1.74	
L	0.30	0.60	0.45	
All Dimensions in mm				

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.59
G	0.11
X1	2.49
X2	0.65
Υ	0.39
С	0.65



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